



# N 沟道增强型场效应晶体管 N-CHANNEL MOSFET FHP100N03D/FHD100N03D

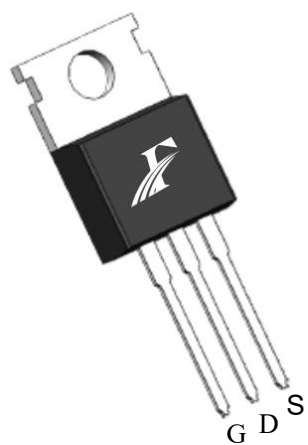
## 主要参数 MAIN CHARACTERISTICS

ID	100 A
VDSS	30 V
Rdson-typ ( @Vgs=10V)	3.8 mΩ
Rdson-typ ( @Vgs=4.5V)	5.1 mΩ
Qg-typ	46 nC

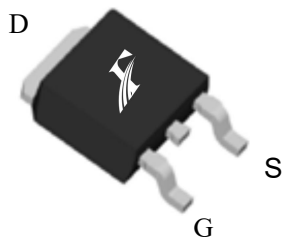
## 用途 APPLICATIONS

功率开关	switch mode power supplies
锂电池保护	BMS
电机控制和驱动	Motor control and drive

## 封装形式 Package



TO-220  
FHP series

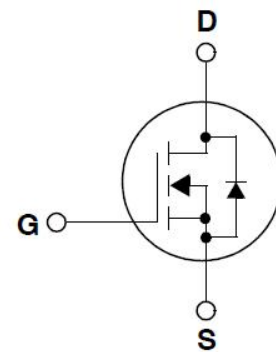


TO-252  
FHD series

## 产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 195 pF)	Low Crss (typical 195pF )
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
100%经过热阻测试	100% DVDS tested
100%经过 Rg 测试	100% Rg tested
RoHS 产品	RoHS product
沟槽工艺	Trench technology

## 等效电路 Equivalent Circuit



## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项目 Parameter	符号 Symbol	数值 Value		单位 Unit
		FHD100N03D	FHP100N03D	
最高漏极-源极直流电压 Drain-Source Voltage	V <sub>DS</sub>	30		V
连续漏极电流* Drain Current -continuous *	I <sub>D</sub> (T <sub>C</sub> =25°C)	100		A
	I <sub>D</sub> (T <sub>C</sub> =100°C)	68		A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	I <sub>DM</sub>	400		A
最高栅源电压 Gate-Source Voltage	V <sub>GS</sub>	±20		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	72		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I <sub>AR</sub>	12		A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	E <sub>AR</sub>	18		mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0		V/ns
耗散功率 Power Dissipation	P <sub>D</sub> (T <sub>C</sub> =25°C)	61	100	W
	-Derate above 25°C	0.48	0.64	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	150, -55~+150		°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300		°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature

## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 <b>Off –Characteristics</b>						
漏-源击穿电压 Drain-Source Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA, referenced to 25°C	-	0.03	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C	-	-	1	μA
		V <sub>DS</sub> =30V, T <sub>C</sub> =125°C	-	-	100	μA
栅极体漏电流 Gate-body leakage current	I <sub>GSS</sub> (F/R)	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
通态特性 <b>On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.6	2.5	V
静态导通电阻 Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A	-	3.8	5.5	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A	-	5.1	7.0	
正向跨导 Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> =10A (note 4)	-	82	-	S
动态特性 <b>Dynamic Characteristics</b>						
栅电阻 Gate Resistance	R <sub>g</sub>	f=1.0MHz, V <sub>DS</sub> OPEN	-	3.5	-	Ω
输入电容 Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	2212	-	pF
输出电容 Output capacitance	C <sub>oss</sub>		-	312	-	
反向传输电容 Reverse transfer capacitance	C <sub>rss</sub>		-	195	-	
开关特性 <b>Switching Characteristics</b>						
延迟时间 Turn-On delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =30A, R <sub>G</sub> =2.7Ω V <sub>GS</sub> =10V (note 4, 5)	-	12	-	ns
上升时间 Turn-On rise time	t <sub>r</sub>		-	97	-	ns
延迟时间 Turn-Off delay time	t <sub>d(off)</sub>		-	39	-	ns
下降时间 Turn-Off Fall time	t <sub>f</sub>		-	107	-	ns
栅极电荷总量 Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V , I <sub>D</sub> =30A, V <sub>GS</sub> =10V (note 4, 5)	-	46	-	nC
栅-源电荷 Gate-Source charge	Q <sub>gs</sub>		-	8	-	nC
栅-漏电荷 Gate-Drain charge	Q <sub>gd</sub>		-	16	-	nC
漏-源二极管特性及最大额定值 <b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		I <sub>S</sub>	-	-	100	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I <sub>SM</sub>	-	-	400	A
正向压降 Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =30A	-	0.8	1.3	V
反向恢复时间 Reverse recovery time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =30A, dI <sub>F</sub> /dt=100A/μs (note 4)	-	21	-	ns
反向恢复电荷 Reverse recovery charge	Q <sub>rr</sub>		-	14	-	nC

## 热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	FHD100N03D	FHP100N03D	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.56	1.2	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	125	62.5	°C/W

注释:

- 1: 脉冲宽度由最高结温限制
- 2: L=1mH, I<sub>AS</sub>=12A, V<sub>DD</sub>=25V, R<sub>G</sub>=25 Ω, 起始结温 T<sub>J</sub>=25°C
- 3: I<sub>SD</sub> ≤100A, di/dt ≤100A/μs, V<sub>DD</sub> ≤B<sub>V</sub>DSS, 起始结温 T<sub>J</sub>=25°C
- 4: 脉冲测试: 脉冲宽度 ≤300μs, 占空比 ≤2%
- 5: 基本与工作温度无关

Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: L=1mH, I<sub>AS</sub>=12A, V<sub>DD</sub>=25V, R<sub>G</sub>=25 Ω, Starting T<sub>J</sub>=25°C
- 3: I<sub>SD</sub> ≤100A, di/dt ≤100A/μs, V<sub>DD</sub> ≤B<sub>V</sub>DSS, Starting T<sub>J</sub>=25°C
- 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%
- 5: Essentially independent of operating temperature

# 特性曲线

## Typical Characteristics

Fig 1: Output Characteristics

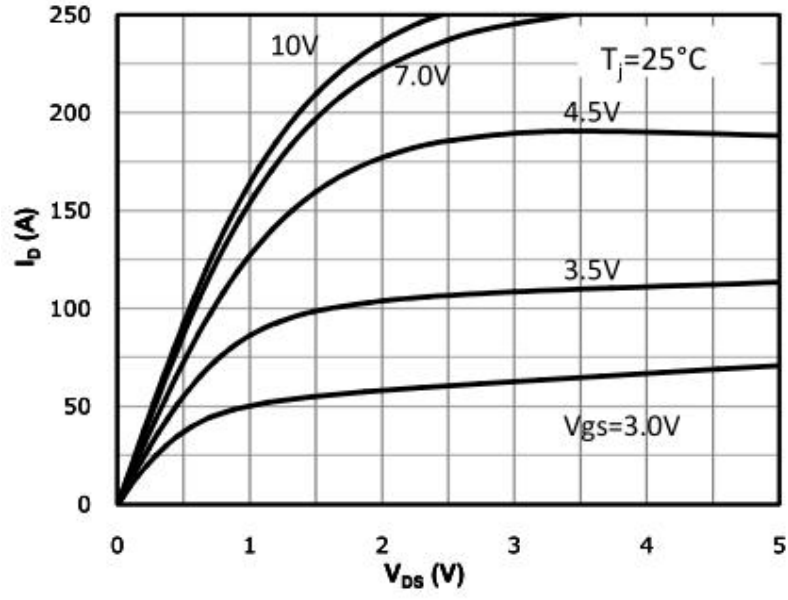


Fig 2: Transfer Characteristics

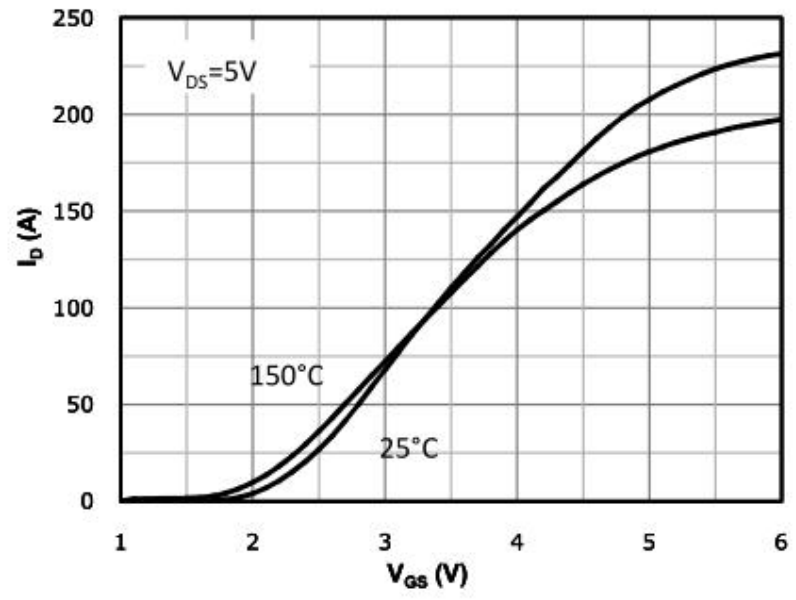


Fig 3: Rds(on) vs Drain Current and Gate Voltage

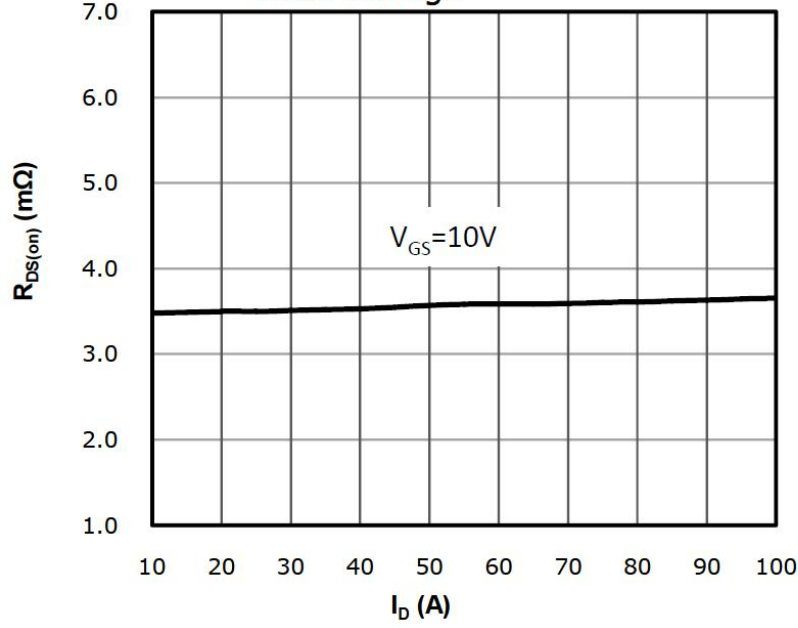


Fig 4: Rds(on) vs Gate Voltage

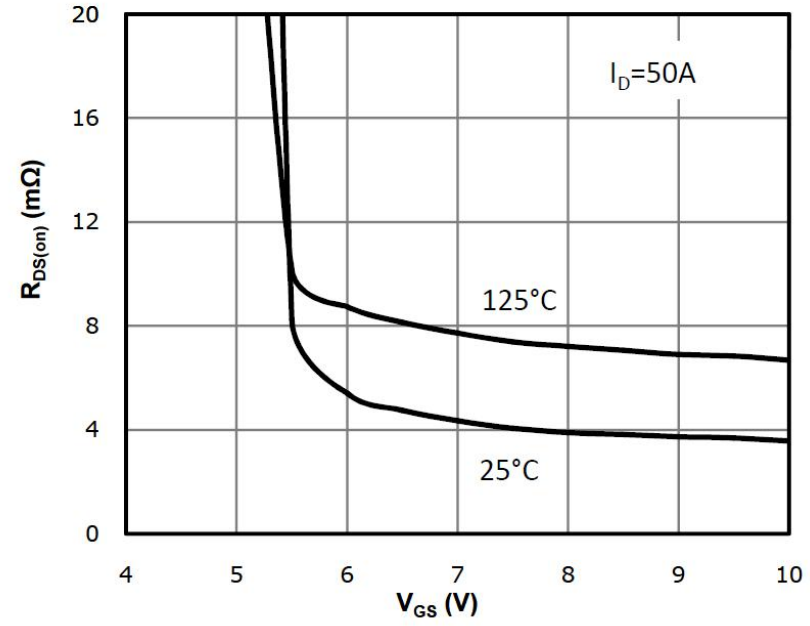


Fig 5: Rds(on) vs. Temperature

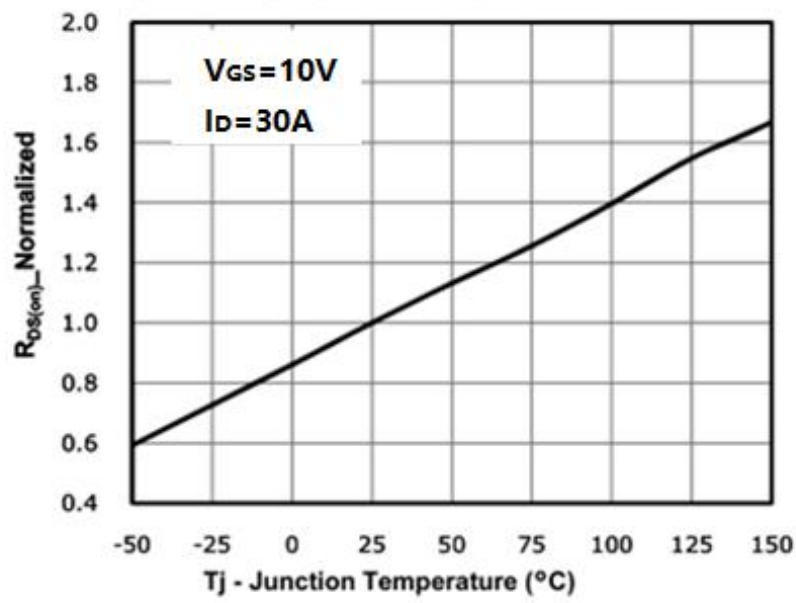
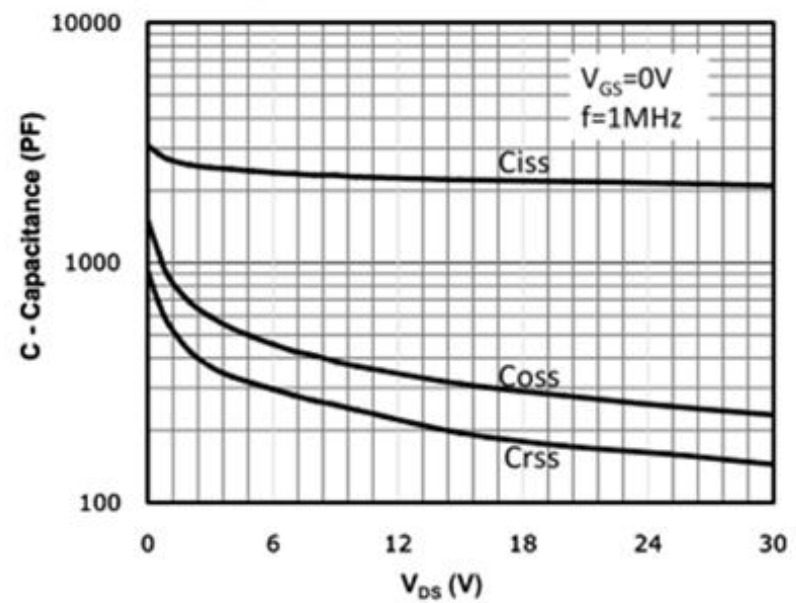
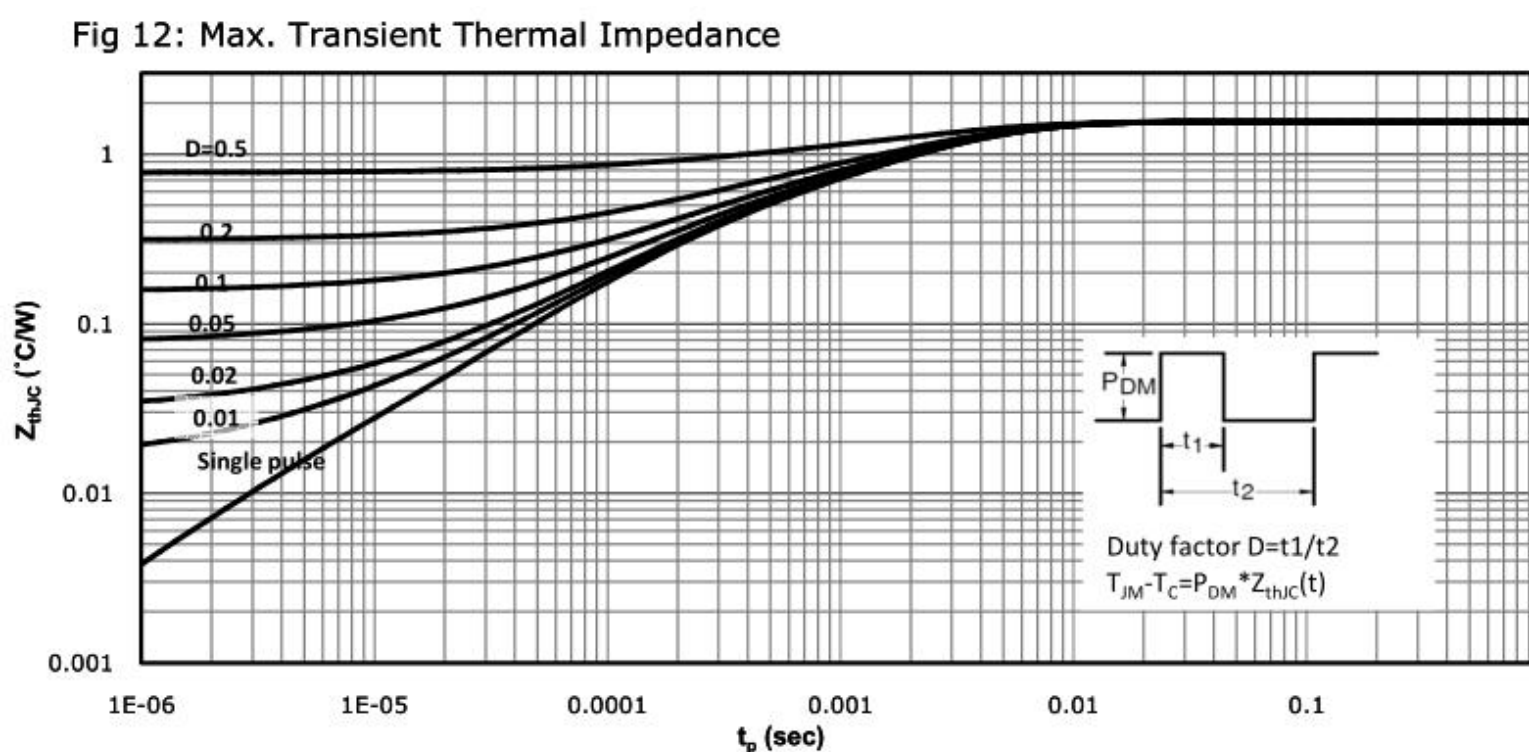
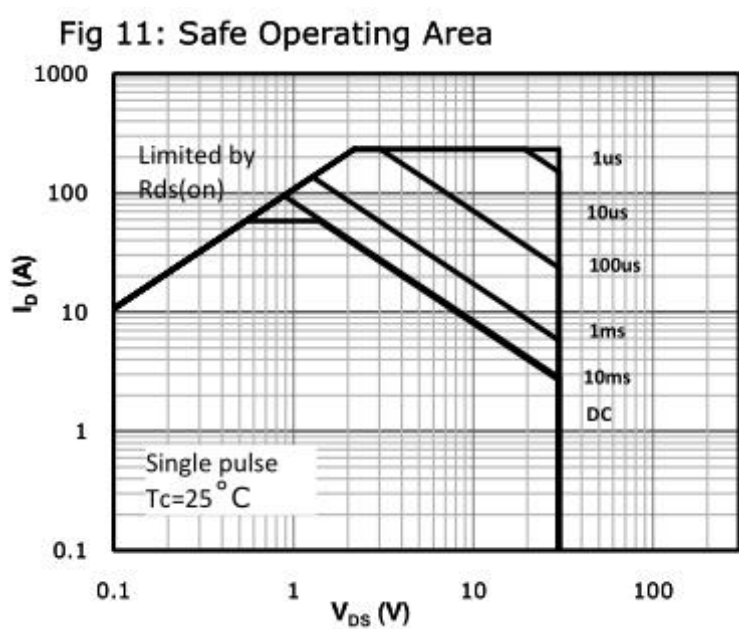
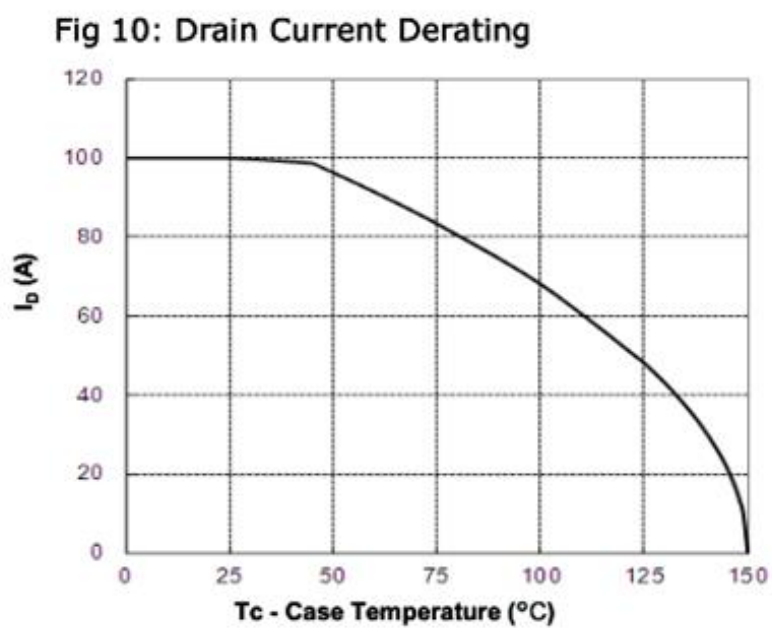
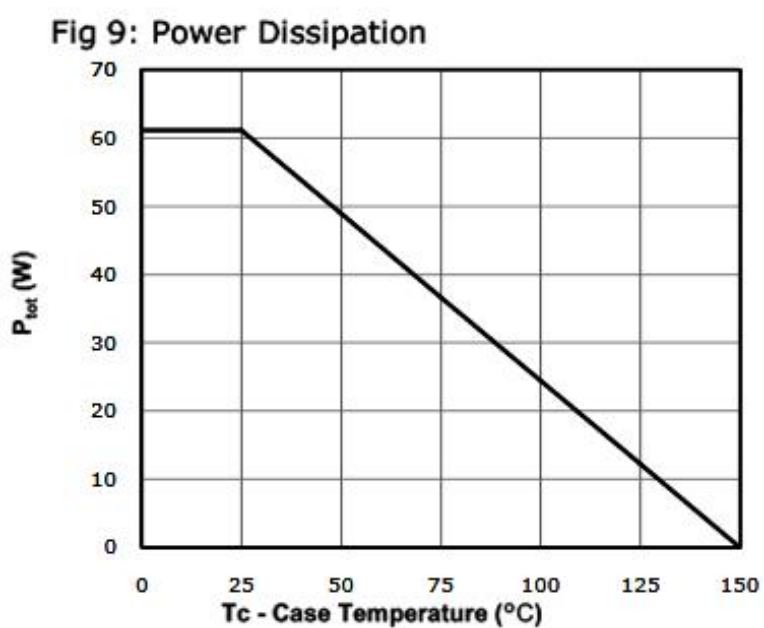
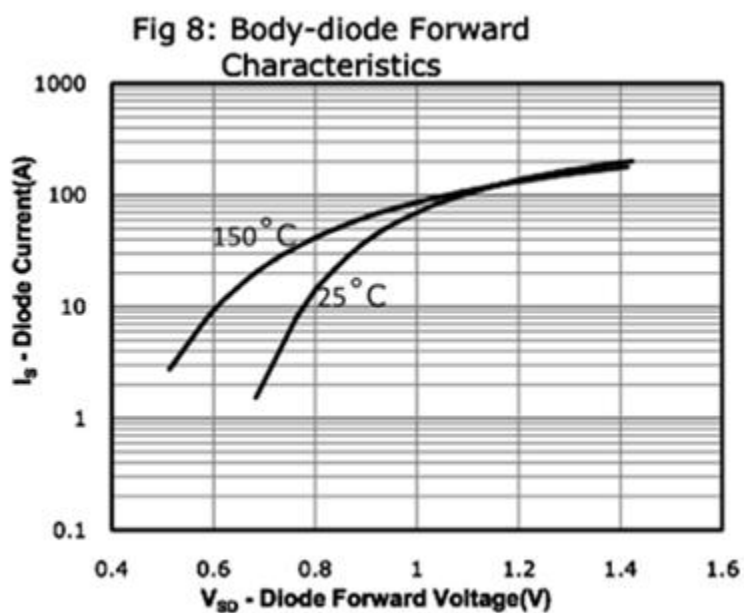
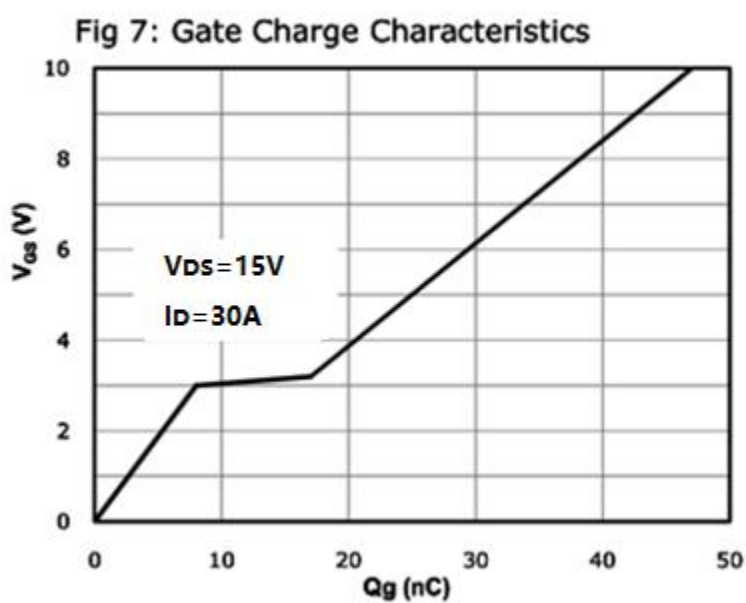


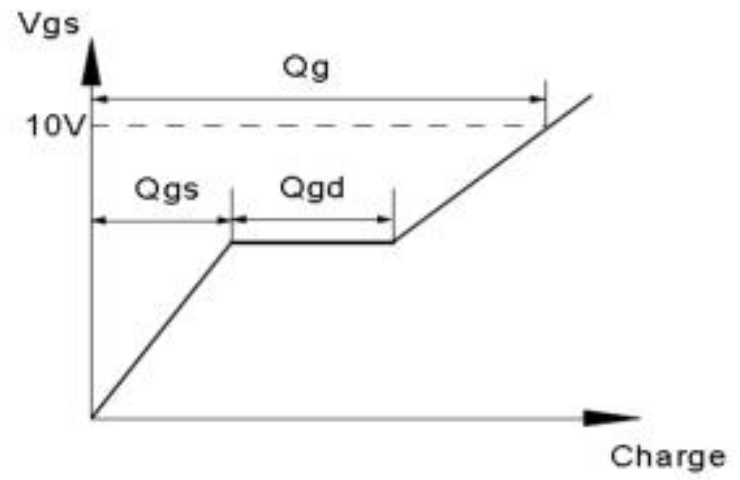
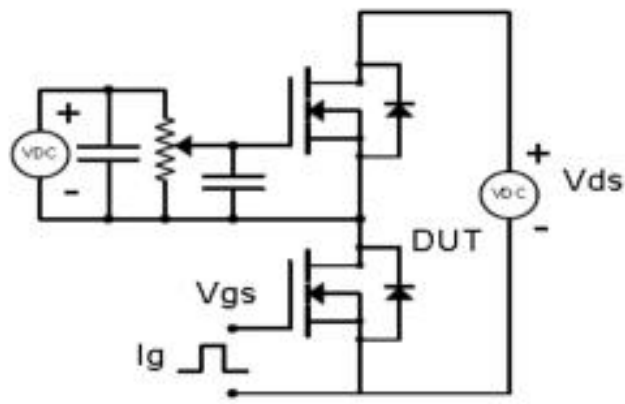
Fig 6: Capacitance Characteristics



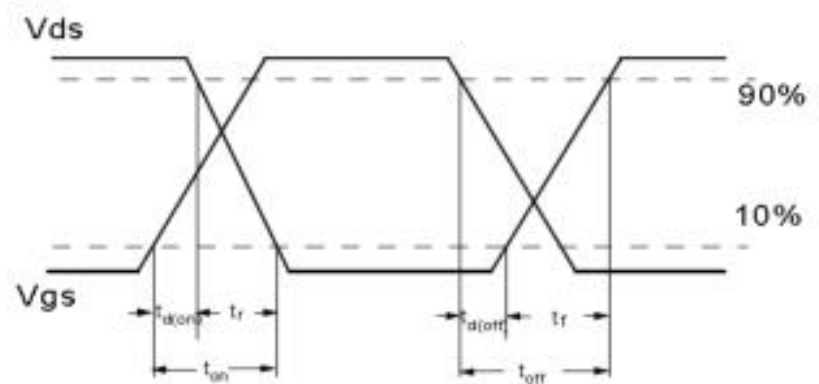
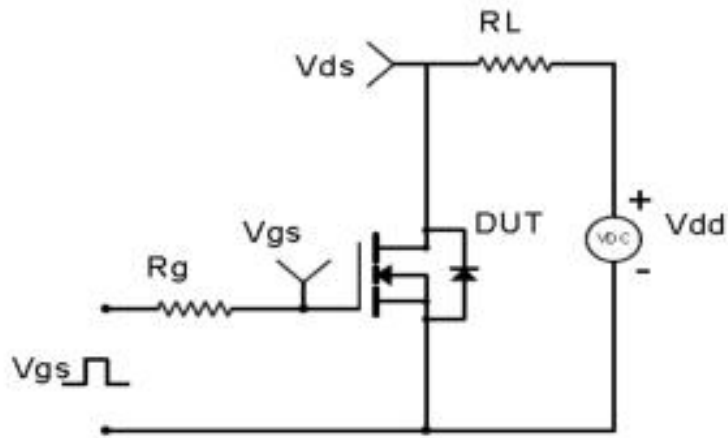


# Test Circuit & Waveform

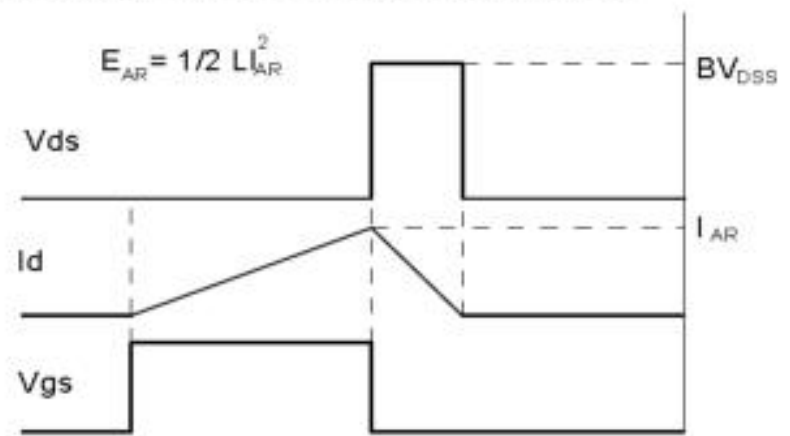
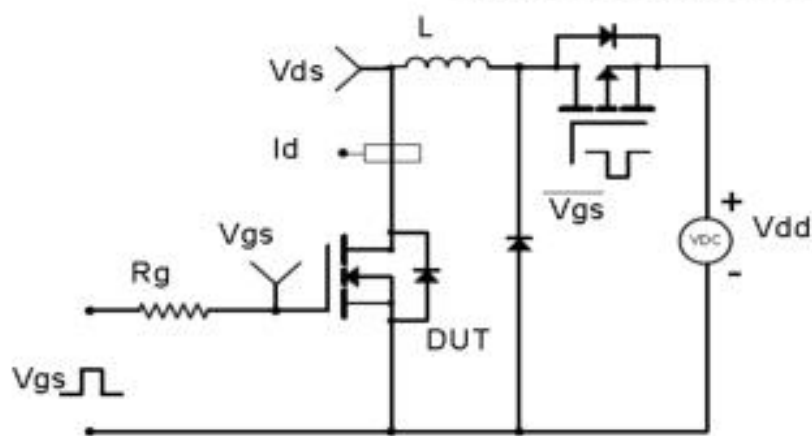
## Gate Charge Test Circuit & Waveform



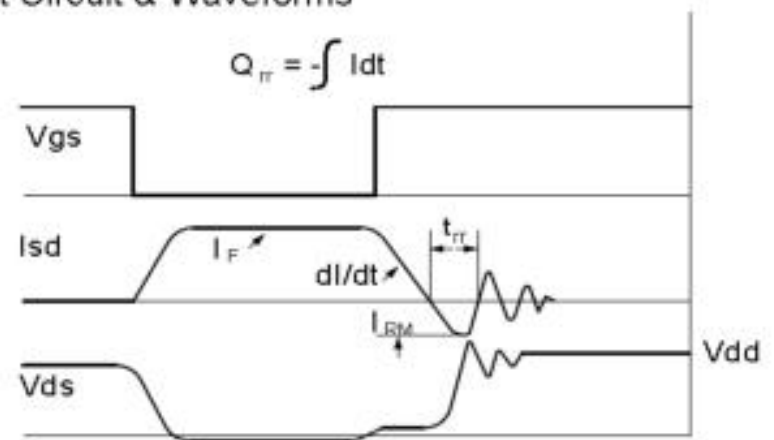
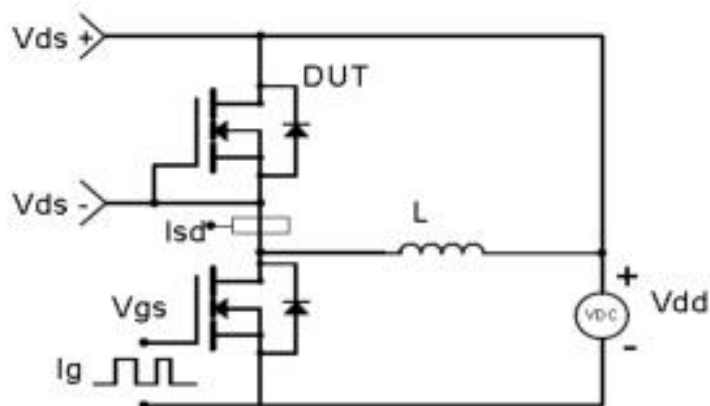
## Resistive Switching Test Circuit & Waveforms



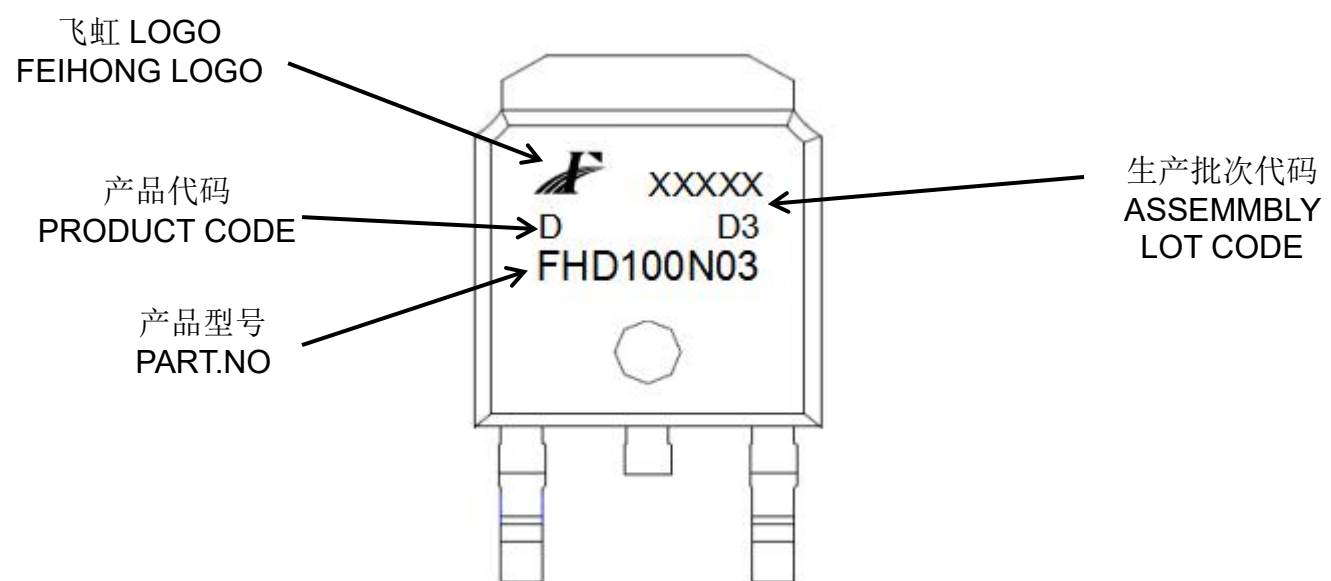
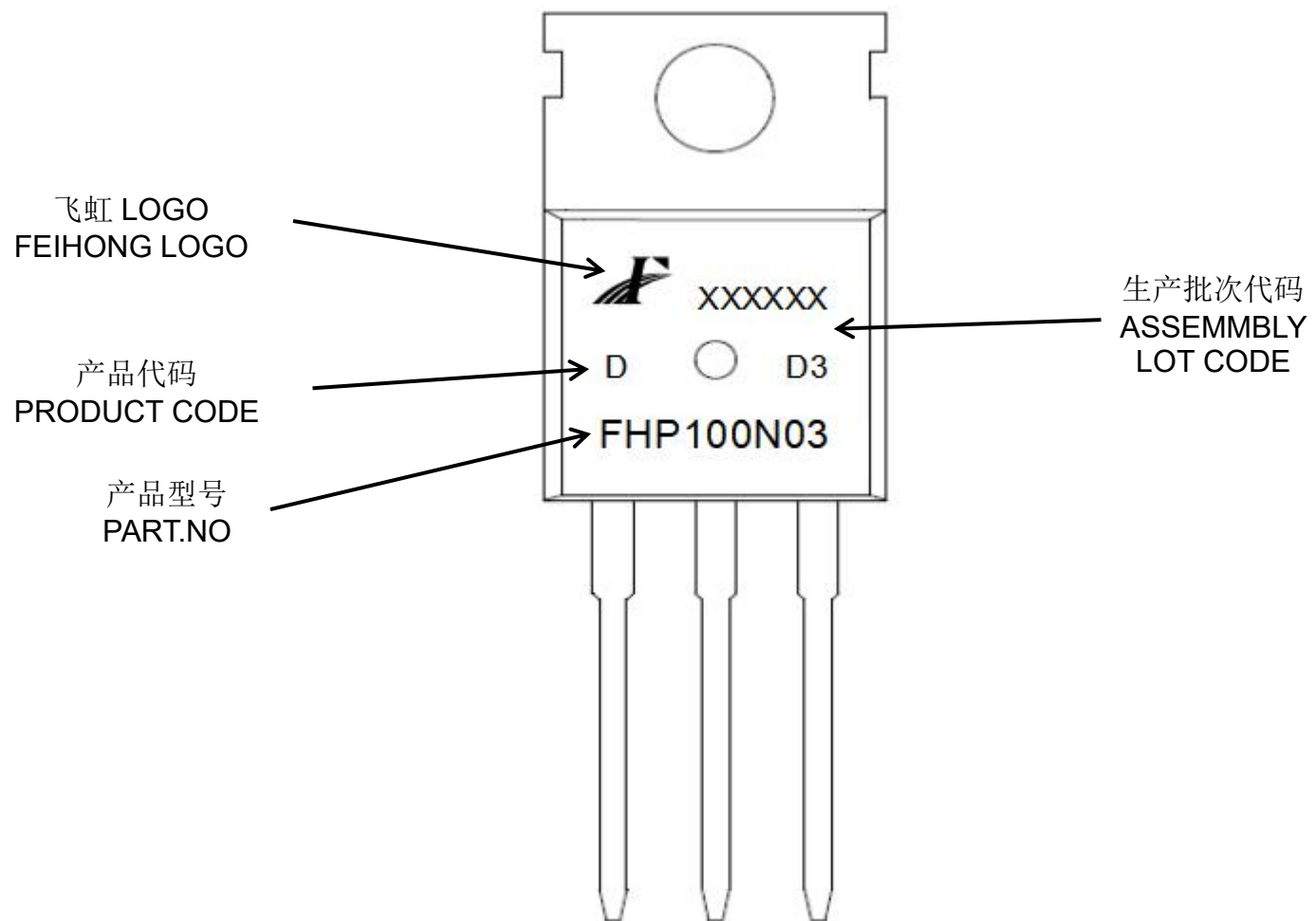
## Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



## Diode Recovery Test Circuit & Waveforms



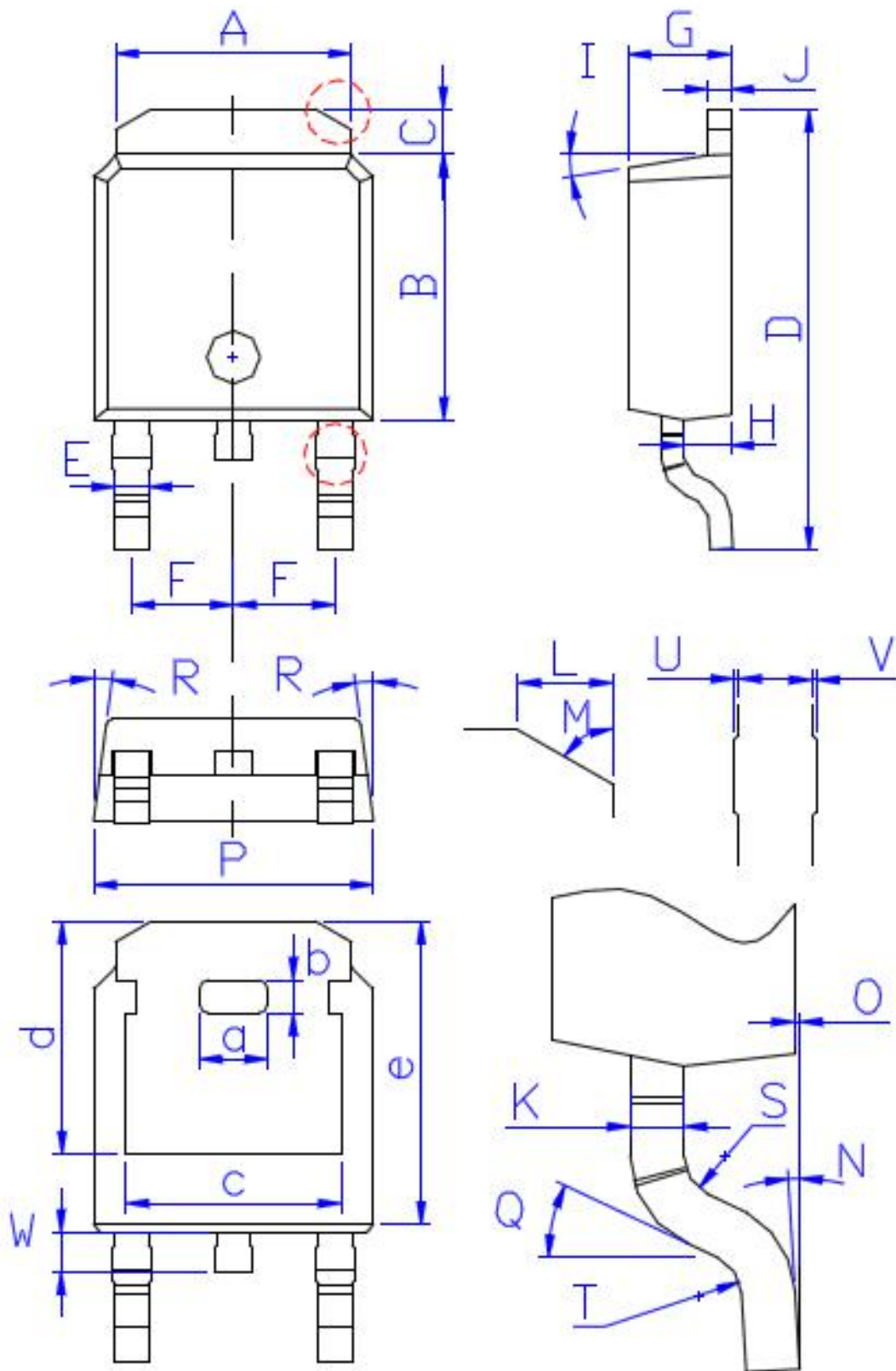
印记 Marking:



外形尺寸:

Package Dimension:

TO-252



DIM	MILLIMETERS
A	5.34±0.30
B	6.00±0.30
C	1.05±0.30
D	9.95±0.30
E	0.76±0.15
F	2.28±0.15
G	2.30±0.30
H	1.06±0.30
I	(4-10)°
J	0.51±0.15
K	0.52±0.15
L	0.80±0.30
M	60°
N	(0-10)°
O	0.05±0.05
P	6.60±0.30
Q	25°
R	(4-8.5)°
S	R0.40
T	R0.40
U	0.05±0.05
V	0.05±0.05
W	0.90±0.30
a	1.80±0.30
b	0.75±0.30
c	4.85±0.30
d	5.30±0.30
e	6.90±0.30

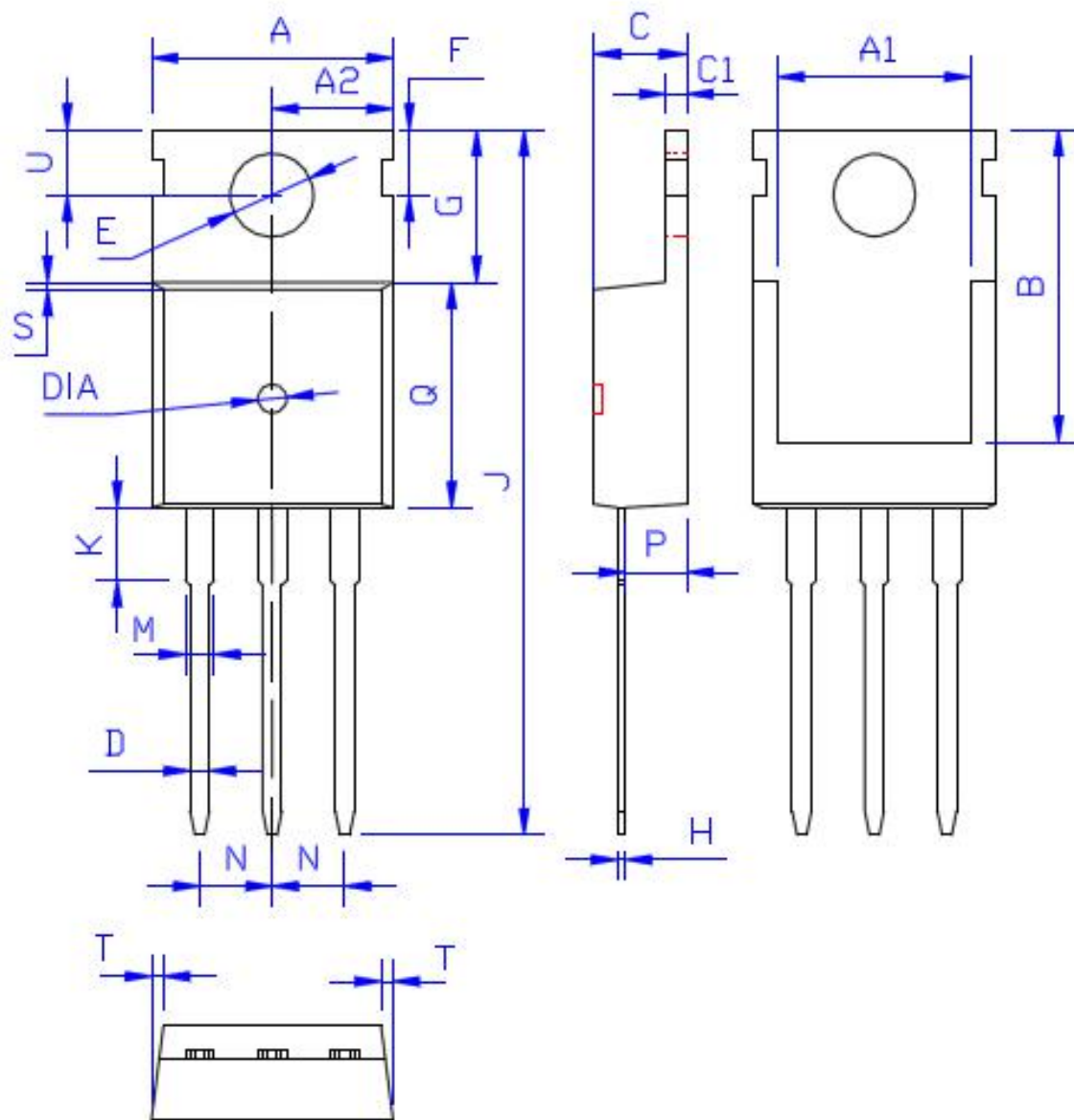
(Units: mm)



外形尺寸:

Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00 ± 0.30
A1	8.00 ± 0.30
A2	5.00 ± 0.30
B	13.20 ± 0.40
C	4.50 ± 0.20
C1	1.30 ± 0.20
D	0.80 ± 0.20
E	3.60 ± 0.20
F	3.00 ± 0.30
G	6.60 ± 0.40
H	0.50 ± 0.20
J	28.88 ± 0.50
K	3.00 ± 0.30
M	1.30 ± 0.30
N	Typical 2.54
P	2.40 ± 0.40
Q	9.20 ± 0.40
S	0.25 ± 0.15
T	0.25 ± 0.15
U	2.80 ± 0.30
DIA	宽 1.50 ± 0.10 深 0.50 MAX

(Unit: mm)